High Current Surface Mount PNP Silicon Switching Transistor for Load Management in Portable Applications

Features

• Pb-Free Package is Available

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	-30	Vdc
Collector-Base Voltage	V _{CBO}	-50	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-1.0	Adc
Collector Current – Peak	I _{CM}	-2.0	Α
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 1)	540 4.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	230	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 2)	925 7.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	135	°C/W
Total Device Dissipation (Single Pulse < 10 s)	P _{Dsingle} (Note 2) (Note 3)	1.3	W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

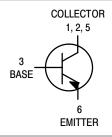
- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 X 1.0 inch Pad
- 3. ref: Figure 8



ON Semiconductor®

http://onsemi.com

30 VOLTS, 2.0 AMPS PNP TRANSISTOR





TSOP-6 CASE 318G STYLE 7

MARKING DIAGRAM



G3 = Specific Device Code

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT6589T1	TSOP-6	3000/Tape & Reel
MMBT6589T1G	TSOP-6 (Pb-Free)	3000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector – Emitter Breakdown Voltage (I _C = –10 mAdc, I _B = 0)	V _{(BR)CEO}	-30	_	Vdc
Collector – Base Breakdown Voltage $(I_C = -0.1 \text{ mAdc}, I_E = 0)$	V _(BR) CBO	-50	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -0.1 \text{ mAdc}, I_C = 0)$	V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	-	-0.1	μAdc
Collector–Emitter Cutoff Current (V _{CES} = -30 Vdc)	I _{CES}	-	-0.1	μAdc
Emitter Cutoff Current (V _{EB} = -4.0 Vdc)	I _{EBO}	-	-0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (Note 4) (Figure 1) $ \begin{aligned} &(I_C = -1.0 \text{ mA}, V_{CE} = -2.0 \text{ V}) \\ &(I_C = -500 \text{ mA}, V_{CE} = -2.0 \text{ V}) \\ &(I_C = -1.0 \text{ A}, V_{CE} = -2.0 \text{ V}) \\ &(I_C = 2.0 \text{ A}, V_{CE} = -2.0 \text{ V}) \end{aligned} $	h _{FE}	100 100 80 40	- 300 - -	
Collector – Emitter Saturation Voltage (Note 4) (Figure 3) ($I_C = -0.5 \text{ A}$, $I_B = -0.05 \text{ A}$) ($I_C = -1.0 \text{ A}$, $I_B = 0.1 \text{ A}$) ($I_C = -2.0 \text{ A}$, $I_B = -0.2 \text{ A}$)	V _{CE(sat)}	- - -	-0.25 -0.30 -0.65	V
Base – Emitter Saturation Voltage (Note 4) (Figure 2) $(I_C = -1.0 \text{ A}, I_B = -0.1 \text{ A})$	V _{BE(sat)}	-	-1.2	V
Base – Emitter Turn–on Voltage (Note 4) (I _C = -1.0 A, V _{CE} = -2.0 V)	V _{BE(on)}	-	-1.1	V
Cutoff Frequency ($I_C = -100 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$, $f = 100 \text{ MHz}$)	f _T	100	-	MHz
Output Capacitance (V _{CB} = -5.0 V, f = 1.0 MHz)	Cobo	-	20	pF

^{4.} Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

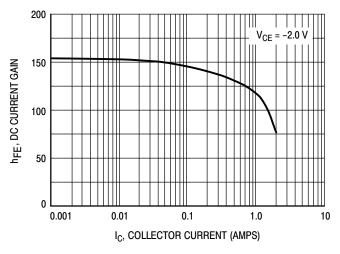


Figure 1. DC Current Gain versus Collector Current

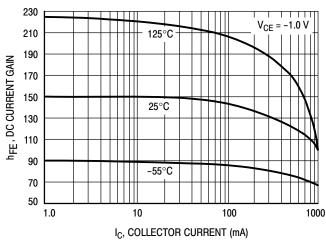


Figure 2. DC Current Gain versus Collector Current

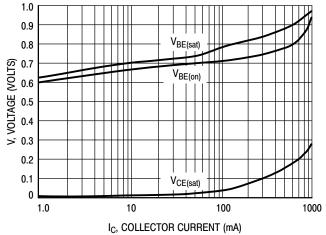


Figure 3. "On" Voltages

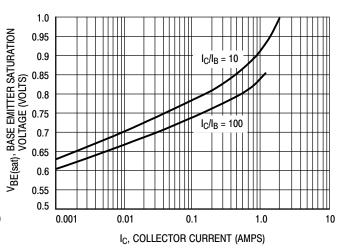


Figure 4. Base Emitter Saturation Voltage versus Collector Current

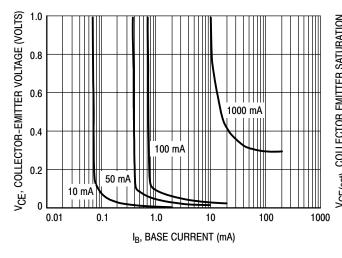


Figure 5. Collector Emitter Saturation Voltage versus Collector Current

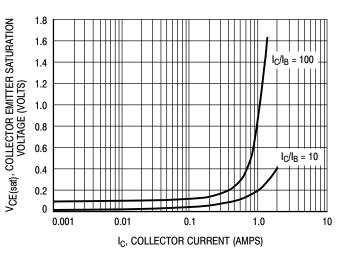


Figure 6. Collector Emitter Saturation Voltage versus Collector Current

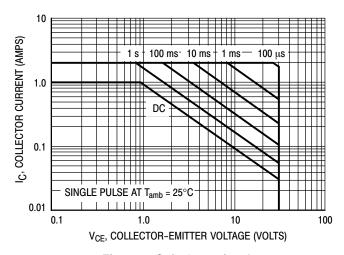


Figure 7. Safe Operating Area

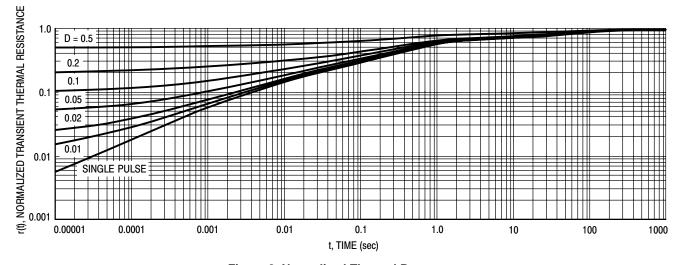


Figure 8. Normalized Thermal Response



TSOP-6 CASE 318G-02 **ISSUE V**

DATE 12 JUN 2012

STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR

3. BASE 4. EMITTER

2. GROUND

3. I/O 4. I/O 5. VCC 6. I/O

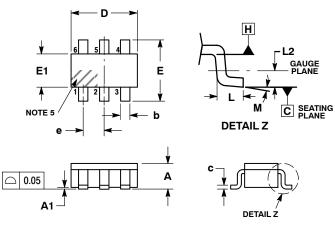
STYLE 12:

5. COLLECTOR 6. COLLECTOR

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
- LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS, MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.90	1.00	1.10	
A1	0.01	0.06	0.10	
b	0.25	0.38	0.50	
С	0.10	0.18	0.26	
D	2.90	3.00	3.10	
E	2.50	2.75	3.00	
E1	1.30	1.50	1.70	
е	0.85	0.95	1.05	
L	0.20	0.40	0.60	
L2	0.25 BSC			
М	0°	-	10°	



STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	2. GND ' 3. D(OUT)- 4. D(IN)- 5. VBUS	SOURCE 2
STYLE 13: PIN 1. GATE 1	STYLE 14: PIN 1. ANODE		LE 16: I 1. ANODE/CATHODE	STYLE 17: PIN 1. EMITTER

2. SOURCE 3. GATE

DRAIN

CATHODE

5. N/C

RECOMMEN SOLDERING FO	
DRAIN 1 6. CATHODE/DF	

3 GATE

5.

SOURCE

CATHODE/DRAIN

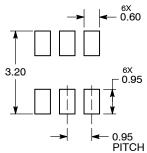
CATHODE/DRAIN

2. SOURCE 2

DRAIN 2

5. SOURCE 1

3 GATE 2



DIMENSIONS: MILLIMETERS

BASE 2. BASE FMITTER 3 ANODE/CATHODE COLLECTOR ANODE CATHODE ANODE

COLLECTOR

GENERIC MARKING DIAGRAM*

M





XXX = Specific Device Code = Date Code

= Pb-Free Package

XXX = Specific Device Code

Α =Assembly Location Υ = Year

W = Work Week

2.

3

5.

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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